

ABSTRACT OF THE DISCLOSURE

A semiconductor laser chip has an active layer, an allover electrode forming a lower face of the laser chip and a light emitting end surface of the laser chip. A Si thin film is formed on the light emitting end surface of the laser chip. An upper Si thin film is formed on an upper portion of the light emitting end surface and a lower Si thin film is formed on a lower portion thereof. The lower Si thin film is smaller in thickness than the upper Si thin film. Smaller thickness of the lower Si thin film prevents a component of the allover electrode from diffusing into the upper Si thin film that covers the active layer. Thus, decrease of a maximum optical output value is prevented, and reliability of the laser chips is increased.